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10EC56

Fifth Semester B.E. Degree Examination, Dec.2017/Jan.2018
Fundamentals of CMOS VLSI

Time: 3 hrs.

Max. Marks: 100

Note: 1. Answer any FIVE full questions, selecting at least TWO questions from each part.
 2. Draw Neat diagram.

PART - A

1. a. Describe with neat diagrams, the P-well fabrication process. (08 Marks)
 b. Explain the DC transfer characteristics of CMOS inverter and mark all the regions of operation with necessary expressions for V_{out} in each region. (08 Marks)
 c. Compare CMOS and Bipolar Technology. (04 Marks)
2. a. Explain Transmission gate and Tristate inverter operations with neat diagram. (06 Marks)
 b. Give the λ -based design rules for different layers, p and n MOSFETS and contact cuts. (08 Marks)
 c. Obtain the stick diagram and layout of two way selector with enable. (06 Marks)
3. a. What are the features of CMOS Domino logic? Explain with neat diagram. (06 Marks)
 b. In the following circuit find V_1, V_2, V_3 and V_4 . (06 Marks)

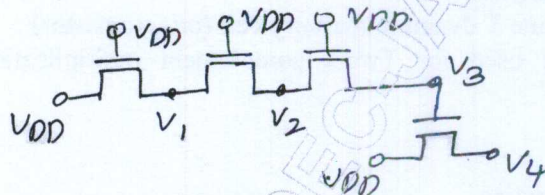


Fig Q3(b) 1

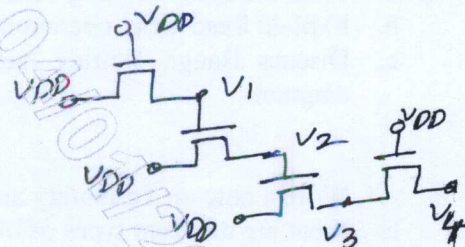


Fig Q3(b) 2

- c. Explain following logic structure with their salient features with neat diagram
 - i) Pseudo nMOS logic
 - ii) C²MOS logic
 (08 Marks)
4. a. Define sheet Resistance and standard unit of capacitance C_g . (06 Marks)
 b. Explain cascaded inverter to drive large capacitance loads? Obtain an equation to find the number of stages. (08 Marks)
 c. Calculate the total capacitance in terms of C_g for the following Fig.Q4(c) (06 Marks)

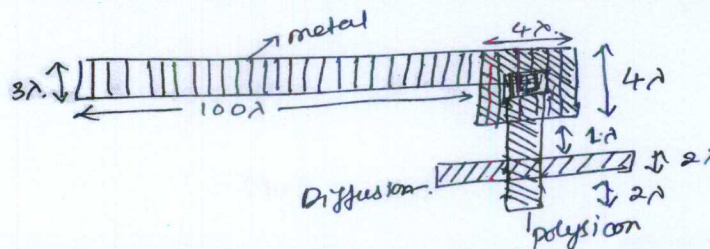


Fig Q4(c)
1 of 2

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
 2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8 = 50, will be treated as malpractice.

PART – B

- 5 a. What are the properties of nMOS and PMOS switches? How TG is useful. (06 Marks)
b. Explain the structure design of a parity generation with necessary diagrams and also write stick diagrams. (08 Marks)
c. Obtain the logic implementation of 4-way multiplexer (Selector) using nMOS switches with necessary diagrams. (06 Marks)
- 6 a. Explain nMOS and CMOS non-inverting dynamic storage cell and draw the 4-bit shift register using nMOS. (07 Marks)
b. How to implement arithmetic and logic operation with a standard adder? Explain with the help of logic expression. (06 Marks)
c. Explain 4×4 Barrel shifter with neat diagram. (07 Marks)
- 7 a. What are system timing consideration? (05 Marks)
b. Explain Read/write operation of one T dynamic memory cell (one transistor). (05 Marks)
c. Discuss Baugh Worley method used for Two's complement multiplication with neat diagrams. (10 Marks)
- 8 a. Write a note on Testability and Testing. (06 Marks)
b. What are different types of I/O pads? (06 Marks)
c. Write short notes on:
i) Built in self Test (BIST)
ii) Scan design Technic. (08 Marks)
